

CMOS 1K-bit serial E²PROM Easy interface with serial port

The S-2917I is a high speed, low power 1K-bit E²PROM that uses the CMOS floating-gate process. Either 64-word × 16-bit or 128-word × 8-bit can be selected. Program operation can be executed continuously.

■ Features

- Low power consumption
Operating: 3.0 mA max.
Standby: 100 μ A max.
- 5-V single power supply
- Write operation with built-in timer
- Chip erase operation
- Continuous instructions are available (except READ)
- Easy interface with serial port
- Rewritings: 10⁴ or 10⁵ times
- Data retention: 10 years

■ Pin Assignment

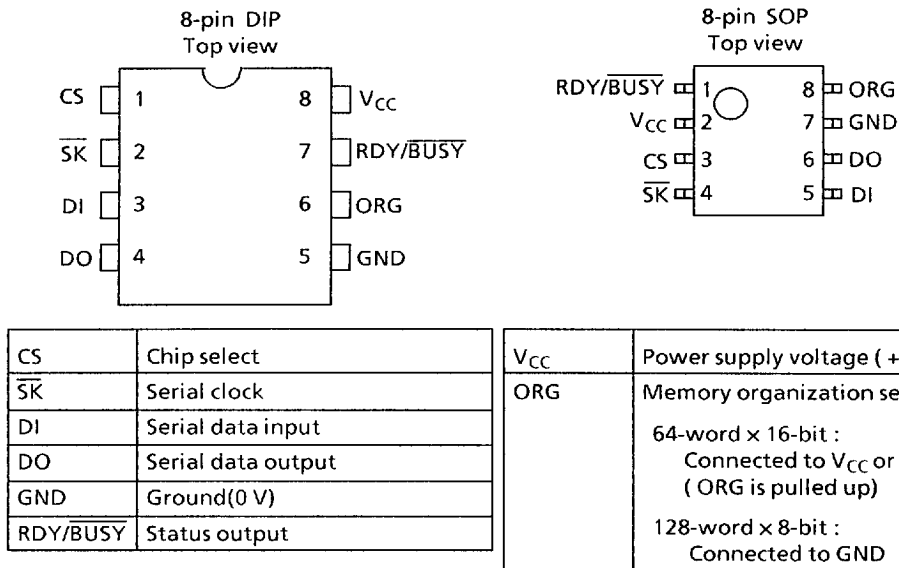


Figure 1

■ Block Diagram

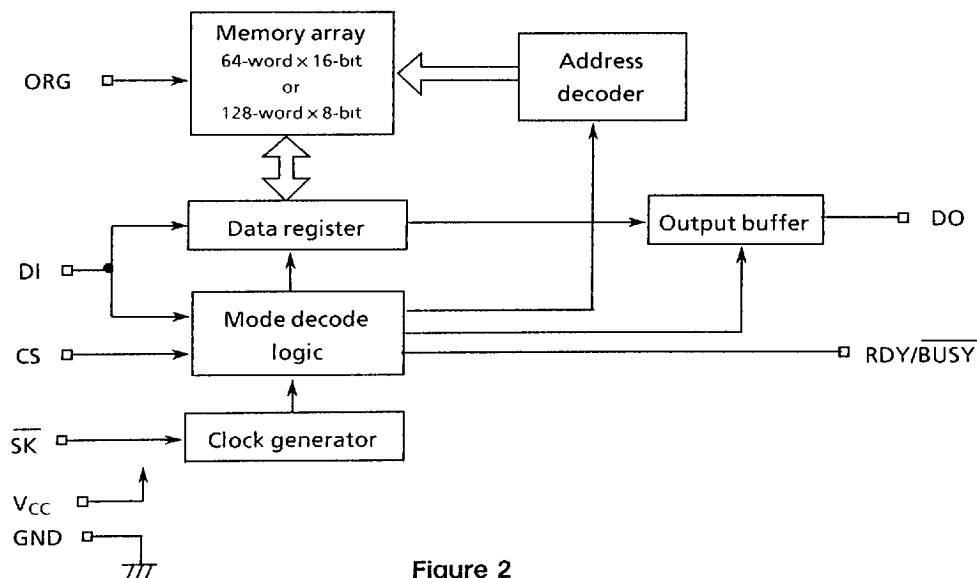


Figure 2

■ Instruction Set

Table 1

Instruction	Start bit	Op code	128-word x 8-bit		64-word x 16-bit	
			Address	Data	Address	Data
READ (Read data)	1	1000xxx	A ₆ to A ₀ x	D ₇ to D ₀	A ₅ to A ₀ xx	D ₁₅ to D ₀
PROGRAM (Program)	1	x100xxx	A ₆ to A ₀ x	D ₇ to D ₀	A ₅ to A ₀ xx	D ₁₅ to D ₀
WRAL (Write all)	1	0001xxx	00000000	D ₇ to D ₀	00000000	D ₁₅ to D ₀
ERAL (Erase all)	1	0010xxx	00000000	—	00000000	—
PEN (Program enable)	1	0011xxx	—	—	—	—
PDS (Program disable)	1	0000xxx	—	—	—	—

x : Don't care

■ Absolute Maximum Ratings

Table 2

Item	Symbol	Ratings	Unit
Power supply voltage	V_{CC}	-0.3 to +7.0	V
Input voltage	V_{IN}	-0.3 to $V_{CC} + 0.3$	V
Output voltage	V_{OUT}	-0.3 to V_{CC}	V
Storage temperature under bias	T_{bias}	-50 to +95	°C
Storage temperature	T_{stg}	-65 to +150	°C

■ Recommended Operating Conditions

Table 3

Item	Symbol	Min.	Typ.	Max.	Unit
Power supply voltage	V_{CC}	4.5	5.0	5.5	V
High level input voltage	V_{IH}	2.0	—	V_{CC}	V
Low level input voltage	V_{IL}	-0.1	—	0.8	V
Operating temperature	T_{opr}	-40	—	+85	°C

DC Electrical Characteristics

Table 4 (Ta = -40°C to 85°C, V_{CC} = +5 V ± 10%)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Current consumption (READ, PEN, PDS)	I _{CC1}	V _{IN} = GND to V _{CC} DO = open	—	—	1.0	mA
Current consumption (PROGRAM, ERAL, WRAL)	I _{CC2}	V _{IN} = GND to V _{CC}	—	—	4.0	mA
Standby current consumption	I _{SB}	CS = GND SK = DI = GND or V _{CC}	—	—	100	μA
Input leakage current	I _{LI}	V _{IN} = V _{CC} , GND	—	0.1	10	μA
Output leakage current	I _{LO}	V _{OUT} = GND to V _{CC} , CS = GND	—	0.1	10	μA
Low level output voltage	V _{OL}	CMOS I _{OL} = 100 μA	—	—	0.1	V
		TTL I _{OL} = 2.1 mA	—	—	0.4	V
High level output voltage	V _{OH}	CMOS I _{OH} = -100 μA	V _{CC} -0.3	—	—	V
		TTL I _{OH} = -400 μA	2.4	—	—	V
Write inhibit voltage	V _{WI}		—	—	3.7	V
Pull-up current for ORG control pin	I _{PU}	ORG pin = GND, V _{CC} = 5.5 V	—	—	10	μA

Rewriting Times

Table 5 (Ta = -40°C to 85°C, V_{CC} = +5 V ± 10%)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Rewriting times	N _W	S-2917101	10 ⁴	—	—	times/word
		S-2917110	10 ⁵	—	—	times/word

Pin Capacitance

Table 6 (Ta = 25°C, f = 1.0 MHz, V_{CC} = 5 V)

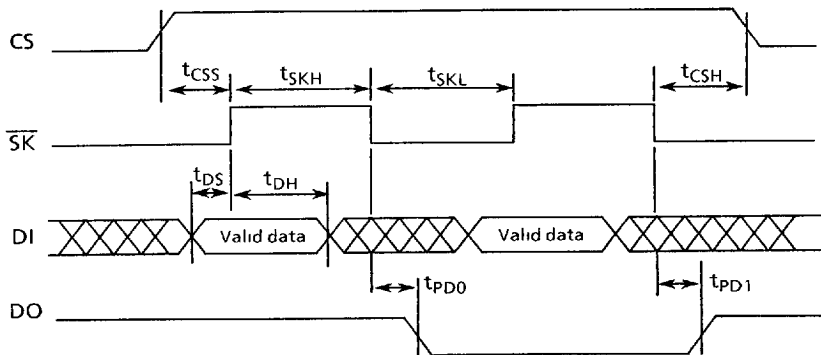
Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input capacitance	C _{IN}	V _{IN} = 0 V	—	—	6	pF
Output capacitance	C _{OUT}	V _{OUT} = 0 V	—	—	10	pF

AC Electrical Characteristics

Table 7

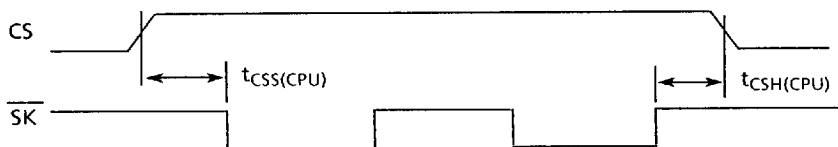
(Ta = -40°C to 85°C, V_{CC} = +5 V ± 10%)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
CS setup time	t _{CSS}	V _{IL} = 0.45 V V _{IH} = 2.40 V CL = 100 pF V _{OL} = 0.80 V V _{OH} = 2.0 V	0.2	—	—	μs
CS hold time	t _{CSH}		0.1	—	—	μs
CS setup time (CPU)	t _{CSS(CPU)}		0.0	—	—	μs
CS hold time (CPU)	t _{CSH(CPU)}		1.0	—	—	μs
Data setup time	t _{DS}		0.2	—	—	μs
Data hold time	t _{DH}		0.2	—	—	μs
1 data output delay	t _{PD1}		0.0	—	0.4	μs
0 data output delay	t _{PD0}		0.0	—	0.4	μs
Clock frequency	f _{SK}		0	—	500	kHz
Clock pulse width	t _{SKH} , t _{SKL}		1.0	—	—	μs
Program time	t _{PR}		—	—	10	ms



Input data is fetched on the rising edge of $\overline{SK}$.
Output data is triggered at the fall of $\overline{SK}$.

Figure 3 Timing chart

Figure 4 Timing chart of t_{CSS(CPU)} and t_{CSH(CPU)} when connecting to CPU

■ Operation

Each of op code with a start bit, address and data is composed of eight bits, and the S-2917I is easily interfaced with a CPU serial I/O port. A start bit is recognized when high of DI is fetched at the rise of the $\overline{SK}$ clock after rising of CS, and operation starts.

Note

- DI must be "L" during verify operation.

(1) Read mode

This mode reads data from a specified address. By the READ instruction, data is triggered at the fall of $\overline{SK}$, and output serially to DO pin.

The READ instruction is executed regardless of program enable or disable mode.

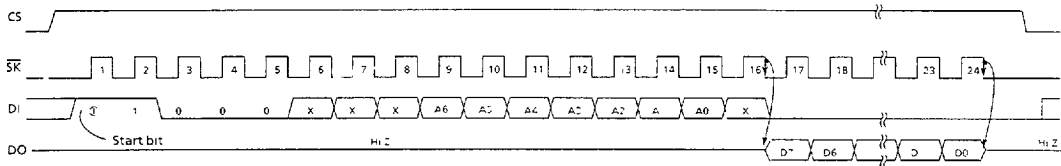


Figure 5 Read mode timing (128-word x 8-bit)

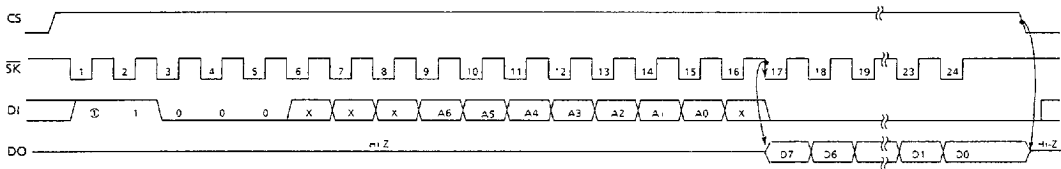


Figure 6 Read mode timing when connected to the CPU (128-word x 8-bit)

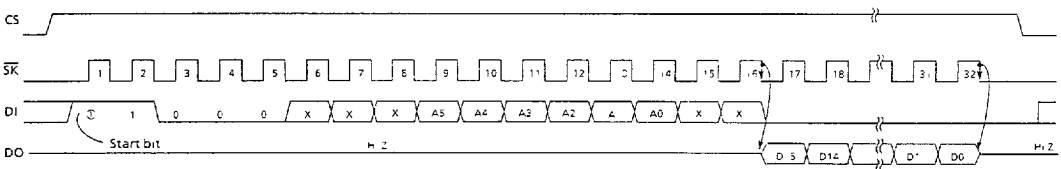


Figure 7 Read mode timing (64word x 16-bit)

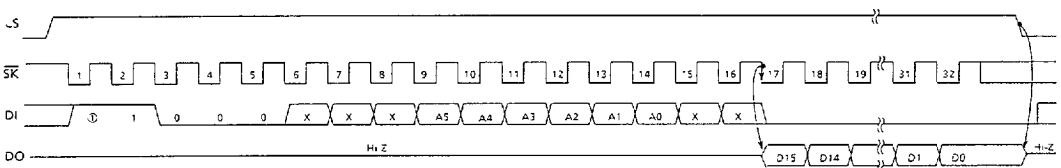


Figure 8 Read mode timing when connected to the CPU (64-word x 16-bit)

(2) Program mode

The PROGRAM instruction, in program enable mode, writes data into the specified address.

When the last data (D0) is fetched into the data register, the data in the specified address is erased and new data is written. This operation is performed by the internal auto-timing generation circuit. During operation, the RDY/BUSY pin goes low, and other instructions cannot be accepted. When the next instruction follows, start that instruction by fetching the start bit after RDY/BUSY goes high.

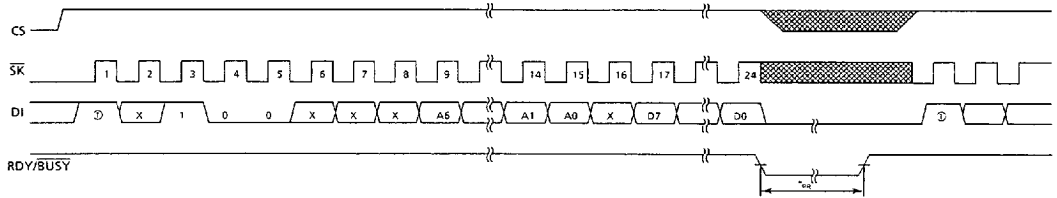


Figure 9 Program mode timing (128-word × 8-bit)

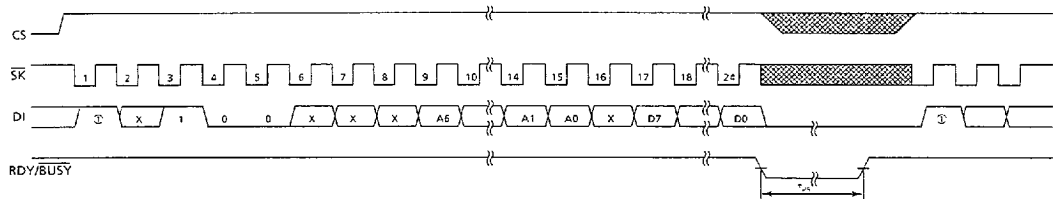


Figure 10 Program mode timing when connected to the CPU (128-word × 8-bit)

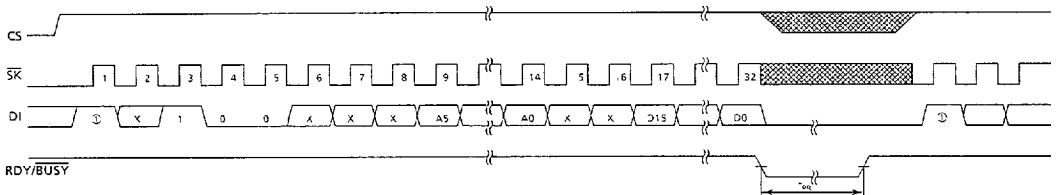


Figure 11 Program mode timing (64-word × 16-bit)

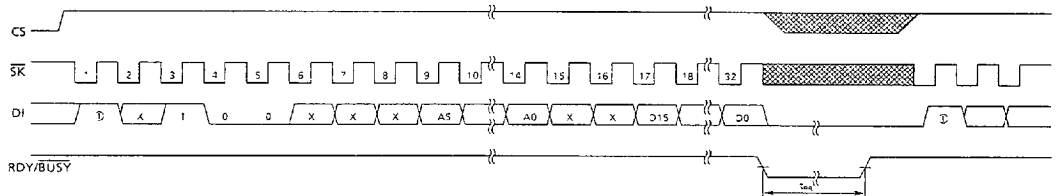


Figure 12 Program mode timing when connected to the CPU (64-word × 16-bit)

(3) Write all (WRAL) mode

In program enable mode, the WRAL instruction puts the S-29171 into write all mode. When the last data (D0) is fetched into the data register, the same data is written into all the addresses of the memory array. This operation is performed by the internal auto-timing generation circuit. During operation, the RDY/ $\overline{\text{BUSY}}$ pin goes low, and other instructions cannot be accepted. When the next instruction follows, start that instruction by fetching the start bit after RDY/ $\overline{\text{BUSY}}$ goes high.

Note: Before executing a WRAL instruction, set all memory array bits to 1.

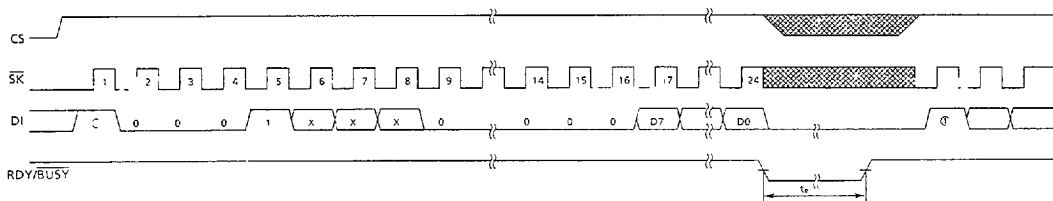


Figure 13 WRAL mode timing (128-word $\times$ 8-bit)

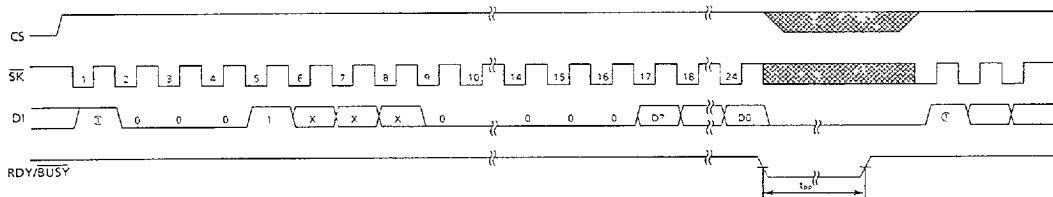


Figure 14 WRAL mode timing when connected to the CPU (128-word $\times$ 8-bit)

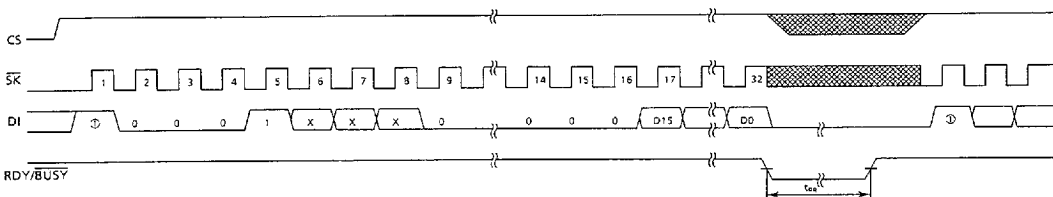


Figure 15 WRAL mode timing (64-word $\times$ 16-bit)

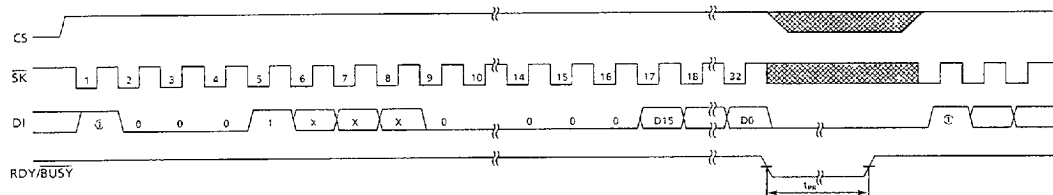
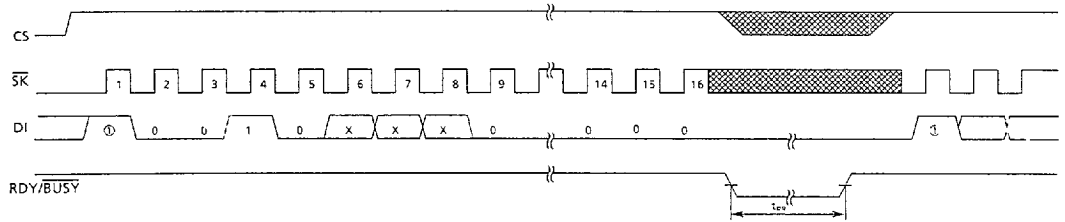
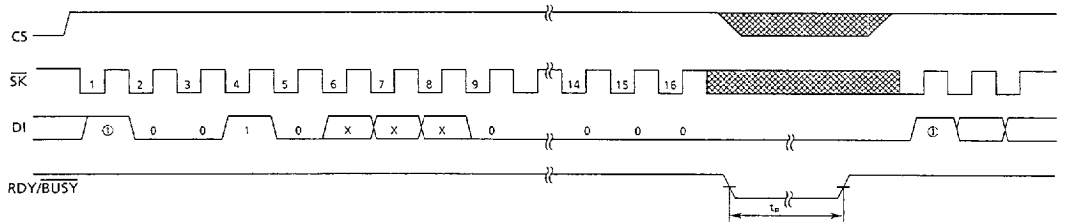
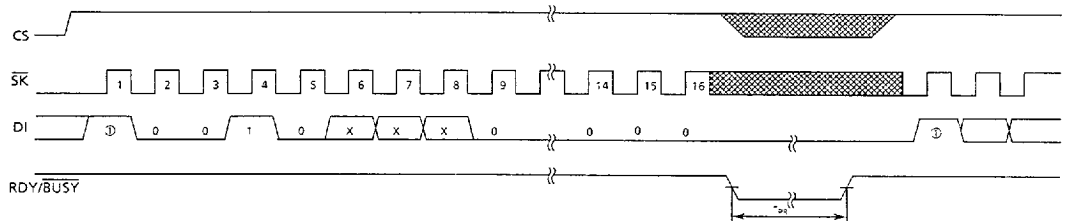
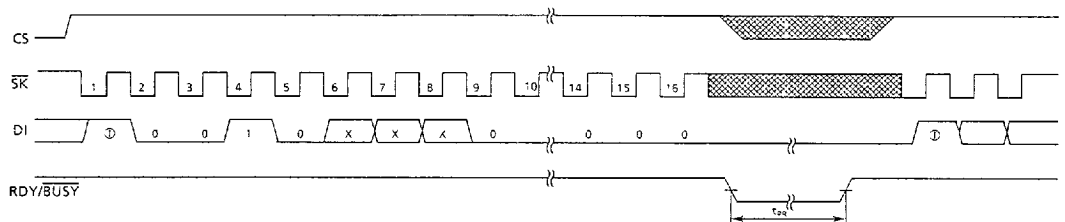


Figure 16 WRAL mode timing when connected to the CPU (64-word $\times$ 16-bit)

(4) Erase all (ERAL) mode

In program enable mode, the ERAL instruction erases the whole of the chip's memory (all memory array bits are set to 1). This operation is performed by the internal auto-timing generation circuit. During operation, the RDY/ $\overline{\text{BUSY}}$ pin goes low and other instructions cannot be accepted. When the next instruction follows, start that instruction by fetching the start bit after RDY/ $\overline{\text{BUSY}}$ goes high.

Figure 17 ERAL mode timing (128-word $\times$ 8-bit)Figure 18 ERAL mode timing when connected to the CPU (128-word $\times$ 8-bit)Figure 19 ERAL mode timing (64-word $\times$ 16-bit)Figure 20 ERAL mode timing when connected to the CPU (64-word $\times$ 16-bit)

S-2917I

(5) Program enable (PEN) and program disable (PDS) modes

The PEN instruction puts the S-2917I into program enable (PEN) mode. In this mode, PROGRAM, WRAL and ERAL instructions are enabled. The S-2917I remains in PEN mode until a PDS instruction is executed. The PDS instruction puts the S-2917I into program disable (PDS) mode. The PROGRAM, WRAL and ERAL instructions are ignored in the PDS mode; this mode is used to protect data against accidental programming.

Note: When power is applied, or the power supply voltage falls below the write inhibit voltage V_{WI} , an internal error protection circuit operates and puts the S-2917I into PDS mode.

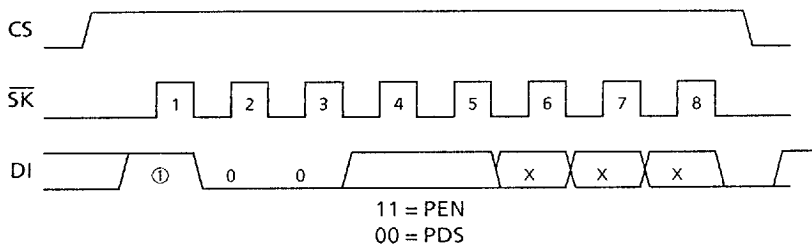


Figure 21 PEN/PDS mode timing

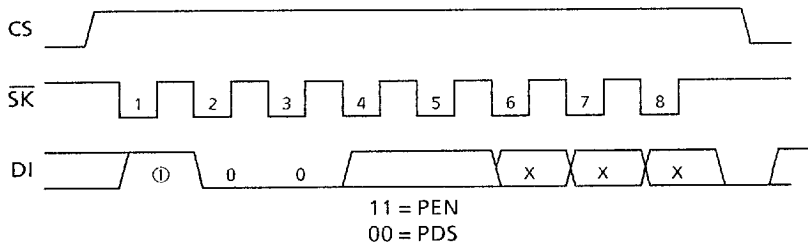


Figure 22 PEN/PDS mode timing when connected to the CPU

(6) Continuous execution

While CS is high, instructions can be continuously executed. An instruction is executed by 8 (including a start bit) $\times n$ ($n = 1, 2, 3 \dots$) $\overline{SK}$. Fetching of the next instruction starts by fetching high of DI (when a start bit is recognized). READ instruction cannot be executed continuously.

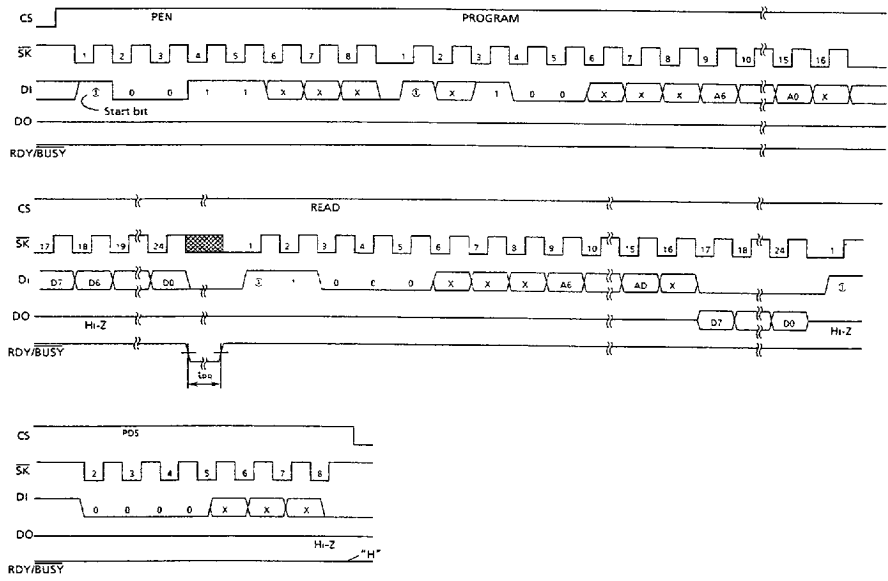


Figure 23 Continuous execution timing (128-word $\times$ 8-bit)

■ Interface with CPU Serial Port

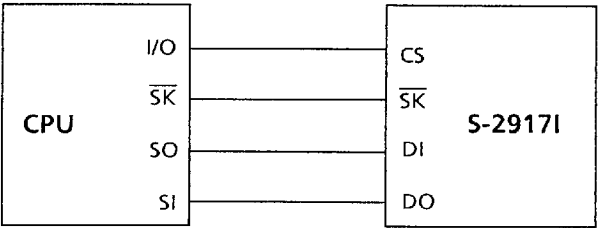


Figure 24 Circuit example

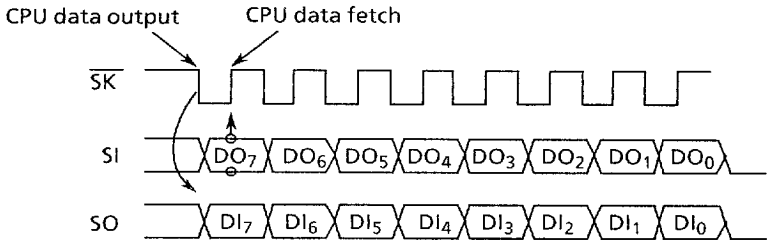


Figure 25 Serial shift timing

S-2917I

■ Dimensions (Unit: mm)

1. S-2917I (8-pin DIP)

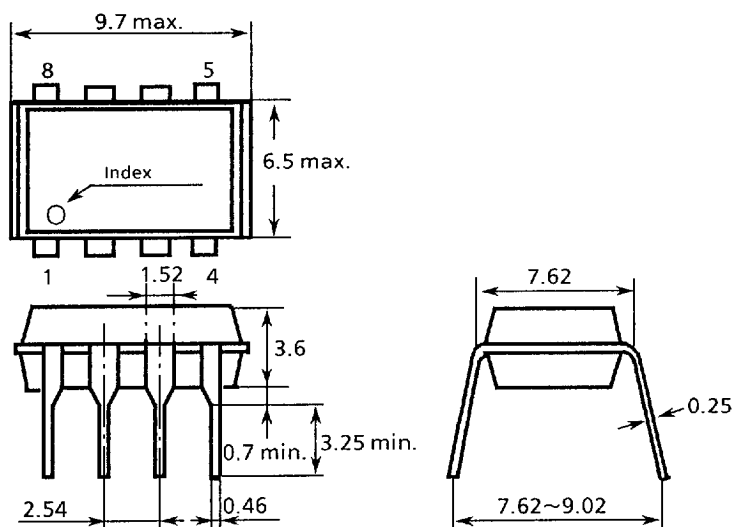


Figure 26

2. S-2917IF (8-pin SOP)

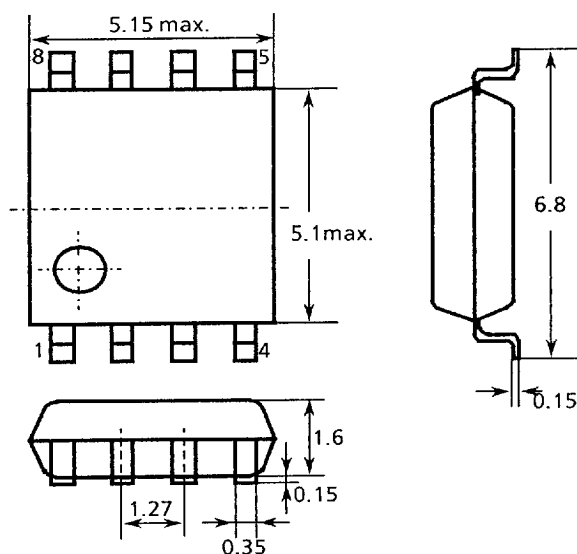


Figure 27

Ordering Information

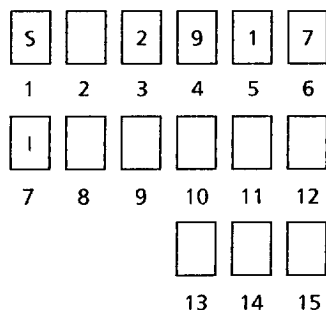
Table 8

Product name	Rewritings / word	Temperature	Package
S-2917I01	10 ⁴	-40°C to 85°C	DIP plastic
S-2917IF01	10 ⁴	-40°C to 85°C	SOP plastic
S-2917I10	10 ⁵	-40°C to 85°C	DIP plastic
S-2917IF10	10 ⁵	-40°C to 85°C	SOP plastic

Note : Each bit is set to 1 before delivery.

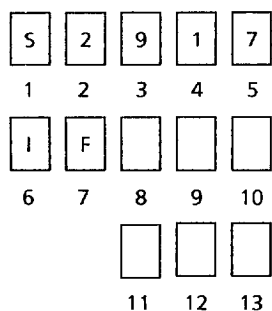
Markings

1. S-2917I (8-pin DIP)



- 1 : S
- 2 : Blank
- 3 to 6 : Product name
- 7 : Temperature range: I = -40 to 85°C
- 8 to 9 : Minimum rewritings : 01 = 10⁴, 10 = 10⁵
- 10 to 12 : Lot No.
- 13 : Assembly mark
- 14 : Last column of year
- 15 : Month of manufacturing: January = 1, February = 2, March = 3, April = 4, May = 5, June = 6, July = 7, August = 8, September = 9, October = X, November = Y, December = Z

2. S-2917IF (8-pin SOP)



- 1 to 5 : Product name
- 6 : Temperature range: I = -40 to 85°C
- 7 : Package: F = SOP
- 8 to 9 : Minimum rewritings : 01 = 10⁴, 10 = 10⁵
- 10 : Assembly mark
- 11 : Month of manufacturing : January = 1, February = 2, March = 3, April = 4, May = 5, June = 6, July = 7, August = 8, September = 9, October = X, November = Y, December = Z
- 12 to 13 : Lot No.

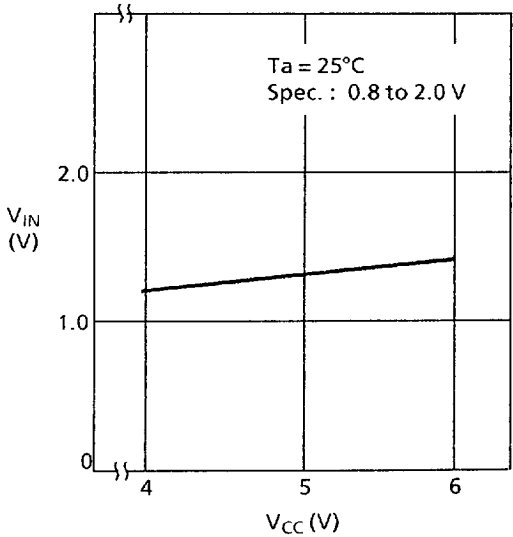
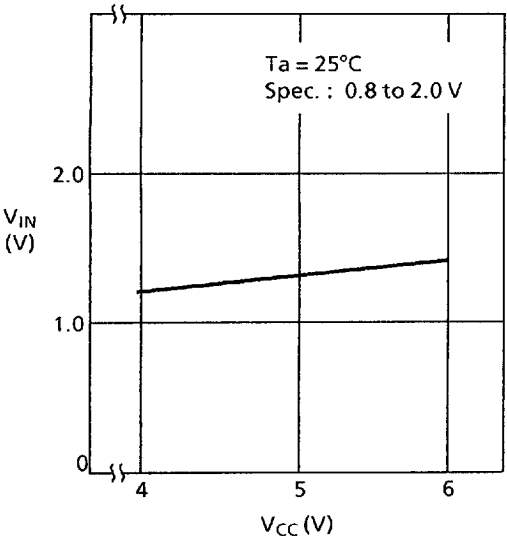
■ Characteristics

1. DC characteristics

1.1 Input voltage (V_{IN})

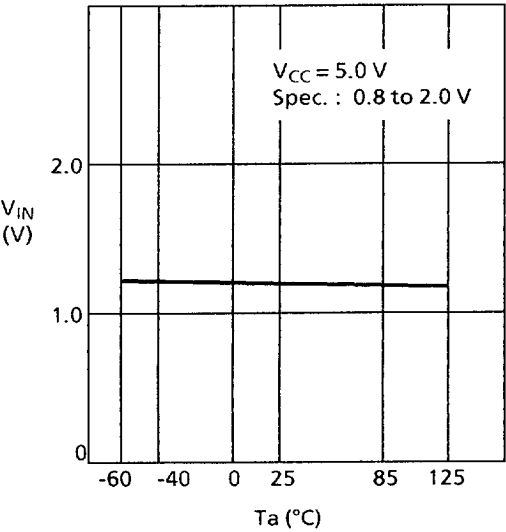
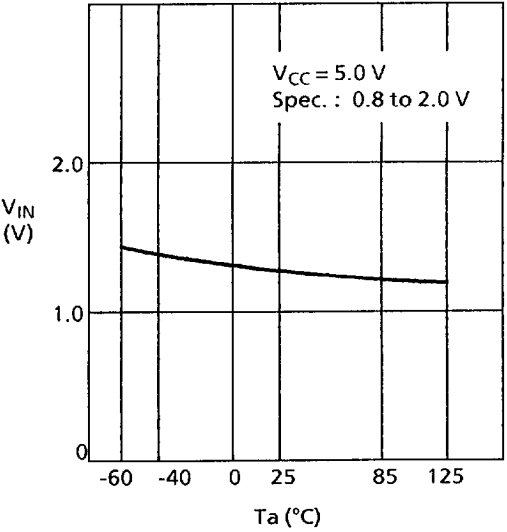
(1) Power supply voltage (V_{CC}) : CS pin

: $\overline{SK}$ pin



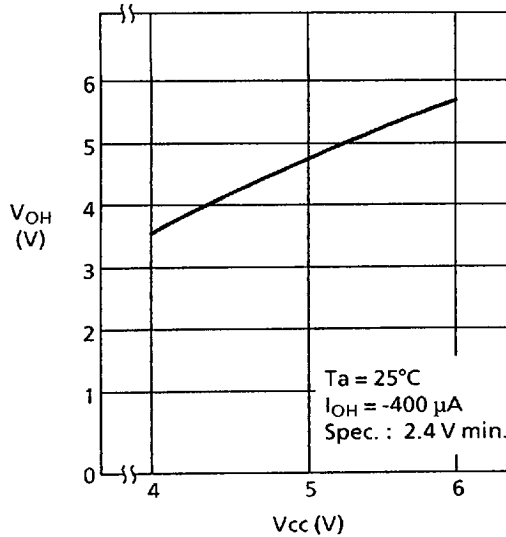
(2) Temperature (T_a) : CS pin

: $\overline{SK}$ pin

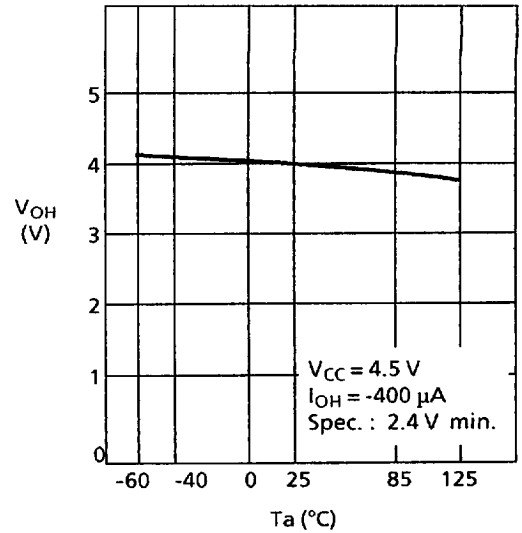


1.2 High level output voltage (V_{OH})

(1) Power supply voltage (V_{CC})

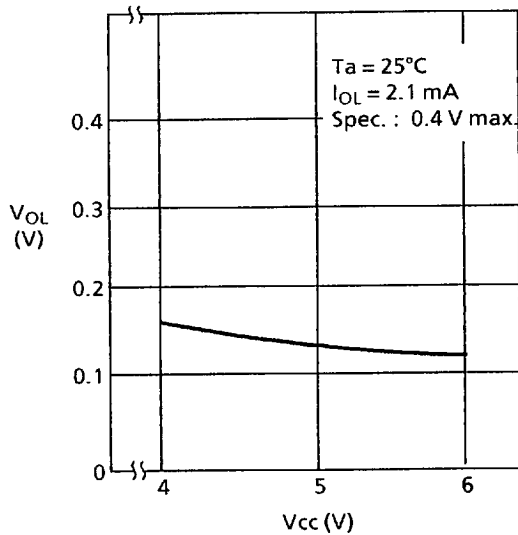


(2) Temperature (T_a)

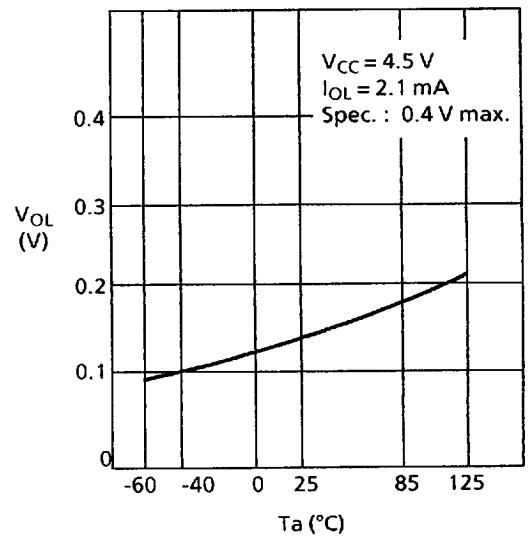


1.3 Low level output voltage (V_{OL})

(1) Power supply voltage (V_{CC})

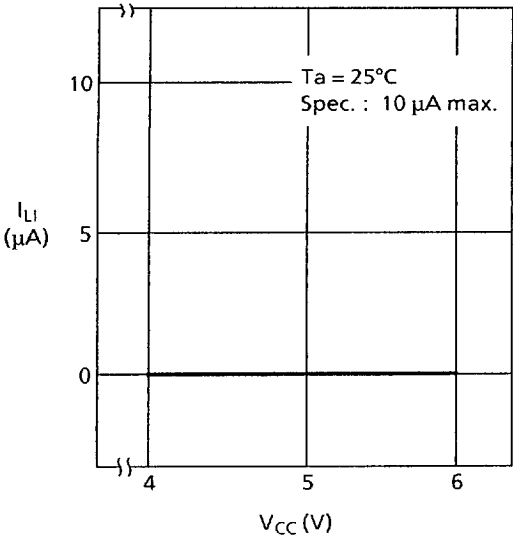


(2) Temperature (T_a)

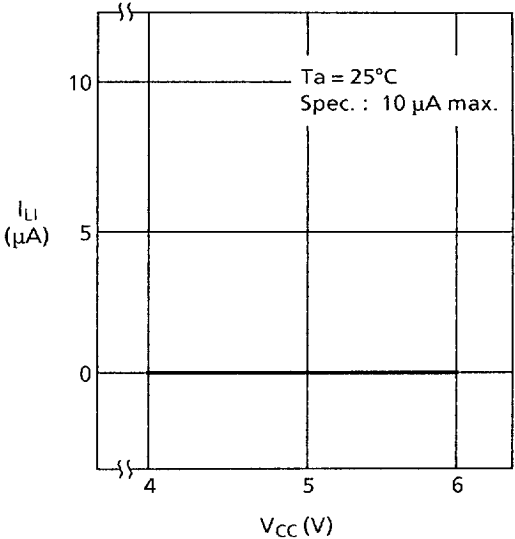


1.4 Input leakage current (I_{LI})

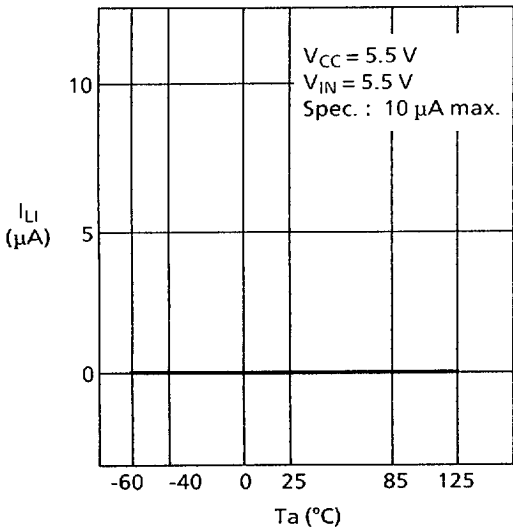
(1) Power supply voltage (V_{CC}) : CS pin



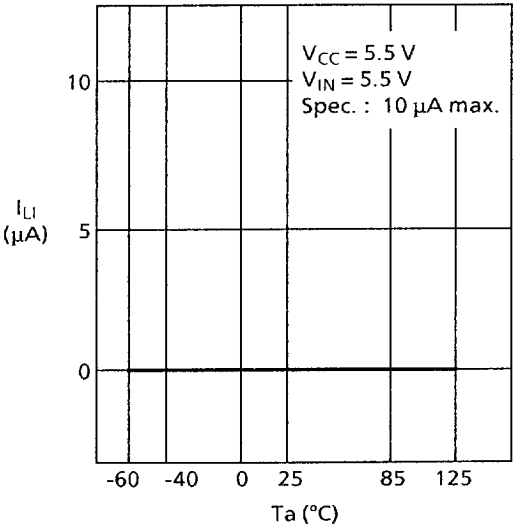
: $\overline{SK}$ and DI pins



(2) Temperature (T_a) : CS pin

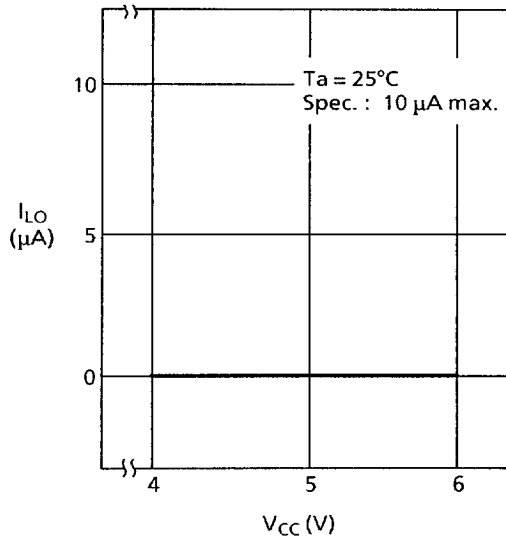


: $\overline{SK}$ and DI pins

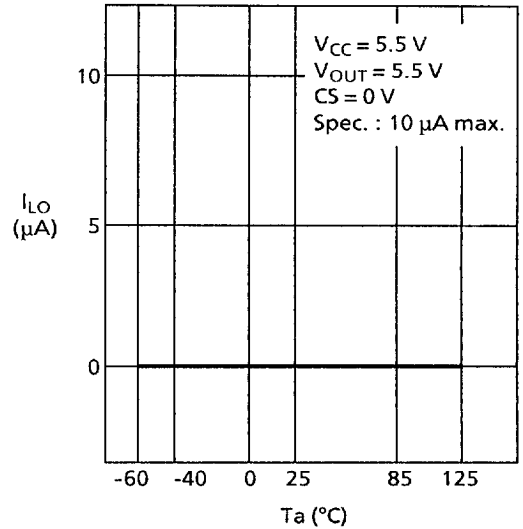


1.5 Output leakage current (I_{LO})

(1) Power supply voltage (V_{CC})

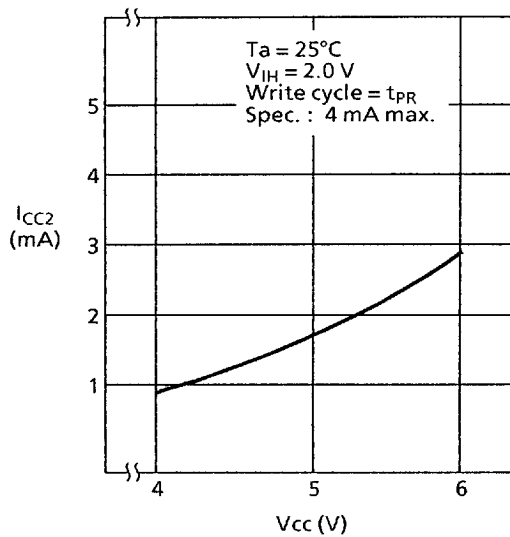


(2) Temperature (T_a) : DO pin

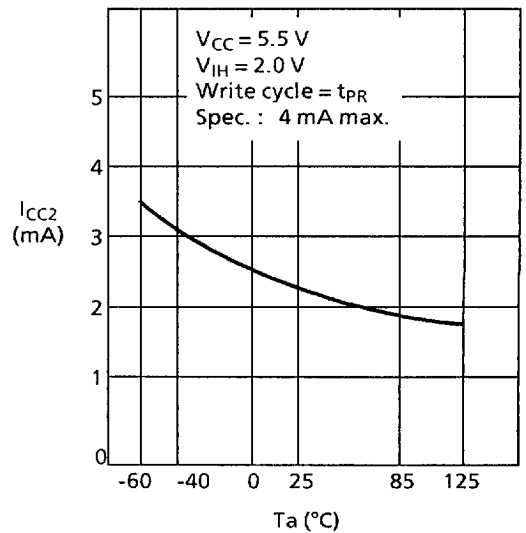


1.6 Writing current consumption (I_{CC2})

(1) Power supply voltage (V_{CC})

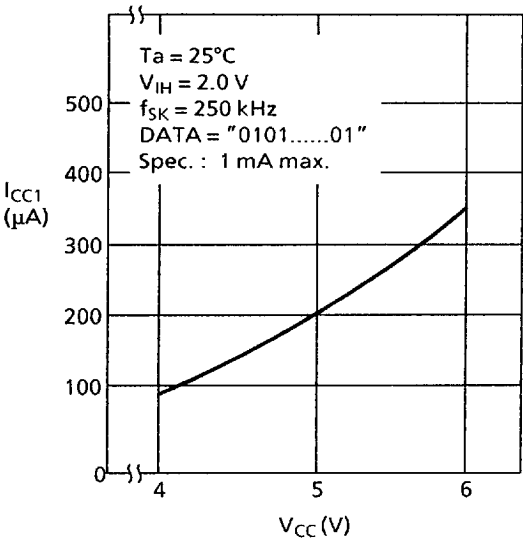


(2) Temperature (T_a)

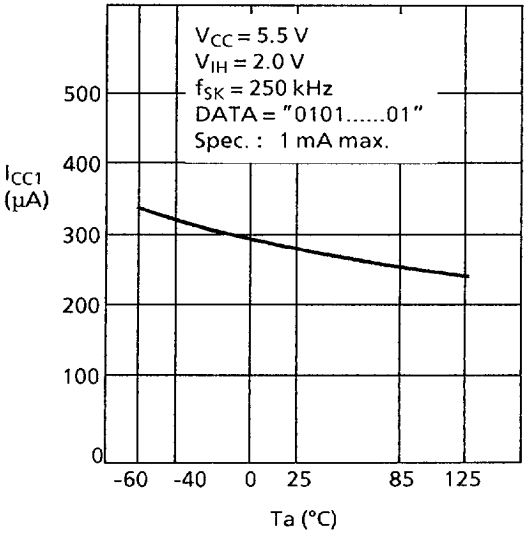


1.7 Reading current consumption (I_{CC1})

(1) Power supply voltage (V_{CC})

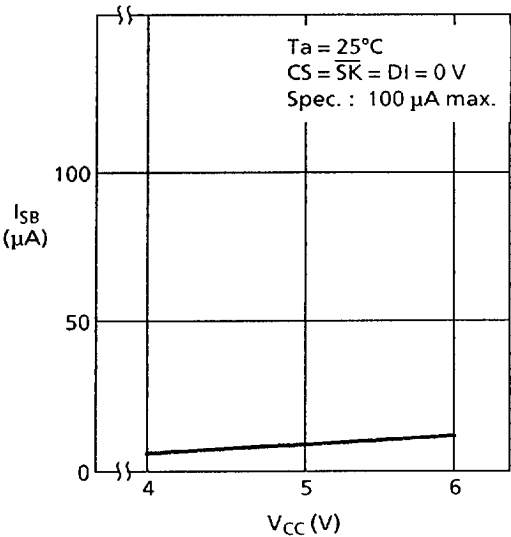


(2) Temperature (T_a)

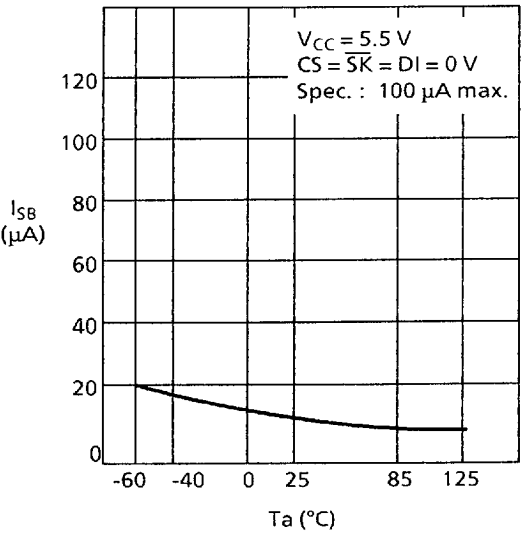


1.8 Standby current consumption (I_{SB})

(1) Power supply voltage (V_{CC})



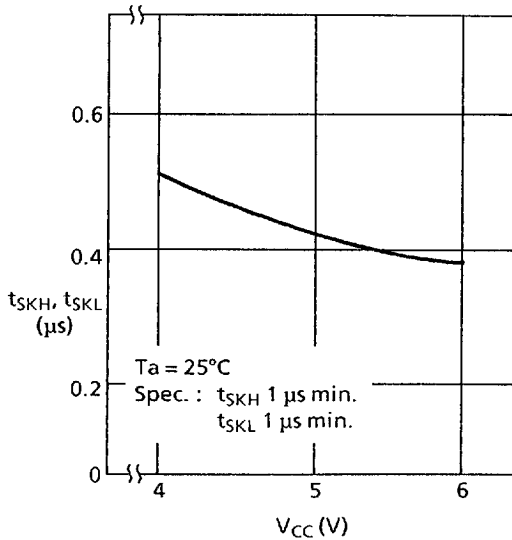
(2) Temperature (T_a)



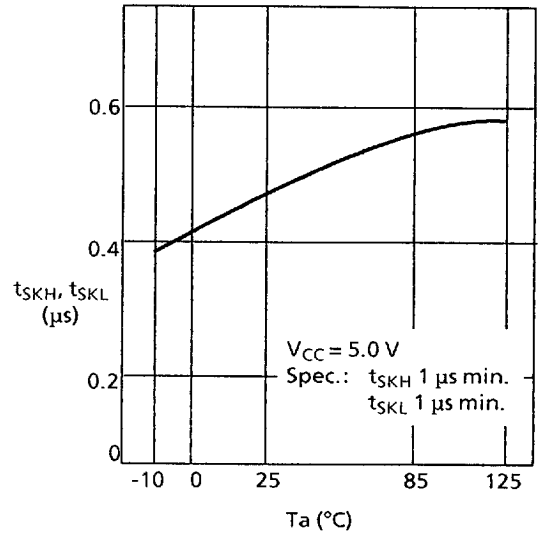
2. AC characteristics

2.1 Clock pulse width (t_{SKH} or t_{SKL})

(1) Power supply voltage (V_{CC})

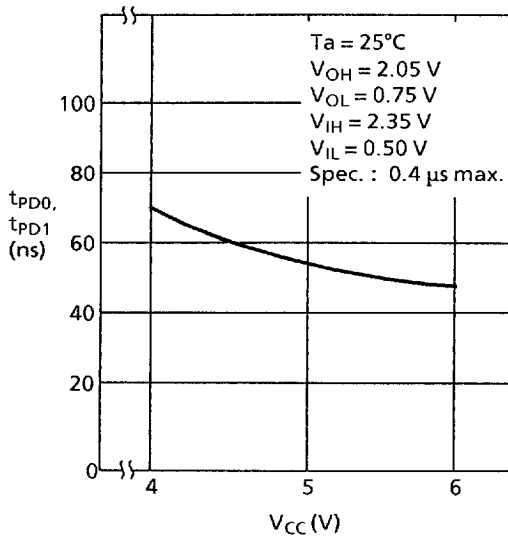


(2) Temperature (T_a)

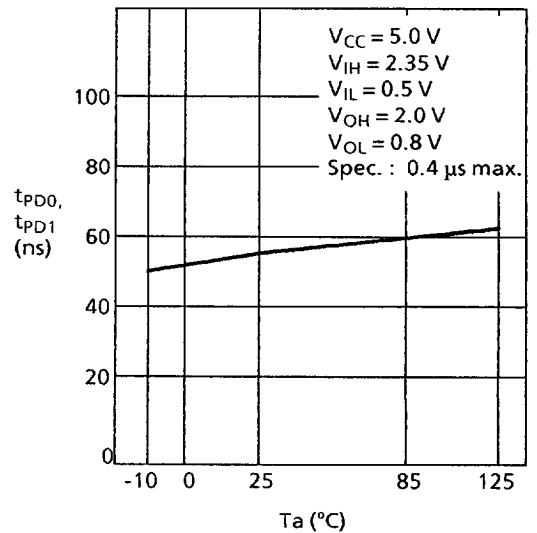


2.2 Data output delay (t_{PD0} or t_{PD1})

(1) Power supply voltage (V_{CC})

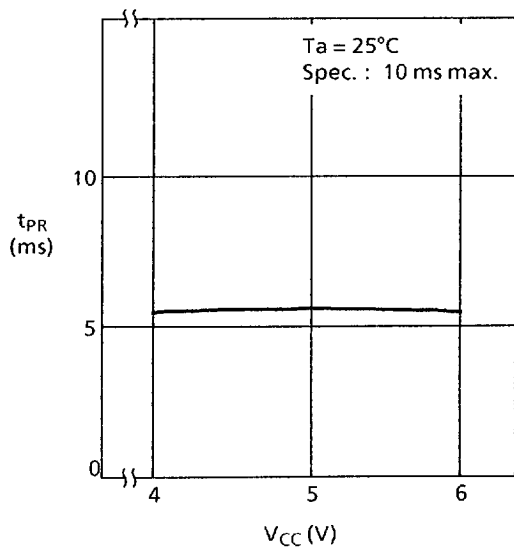


(2) Temperature (T_a)



2.3 Program time (t_{PR})

(1) Power supply voltage (V_{CC})



(2) Temperature (T_a)

